

# P100A - P100M

## **AXIAL LEADED SILICON ZENER DIODES**

VOLTAGE RANGE: 50 - 1000V CURRENT: 1.0 A

#### **Features**

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

#### **Mechanical Data**

Case: D O - 4 1 Molded Plastic

Terminals: Plated Leads Solderable per

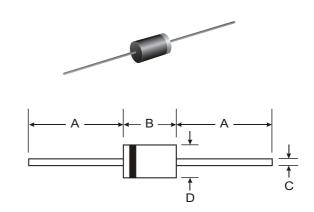
MIL-STD-202, Method 208

Polarity: Cathode Band

• Weight: 0.34 grams (approx.)

Mounting Position: AnyMarking: Type Number





DO-41								
Dim	Min	Max						
Α	25.40	_						
В	4.06	5.21						
С	0.71	0.864						
D	2.00	2.72						
All Dimensions in mm								

### Maximum Ratings and Electrical Characteristics T<sub>A</sub> = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	P100A	P100B	P100D	P100G	P100J	P100K	P100M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	<b>V</b>
Average Rectified Output Current (Note 1) @T <sub>A</sub> = 75°C	lo	1.0					Α		
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	30						Α	
Forward Voltage @I <sub>F</sub> = 1.0A	VFM	1.0					V		
	lгм	5.0 50					μA		
Typical Junction Capacitance (Note 2)	Cj	15				pF			
Typical Thermal Resistance Junction to Ambient (Note 1)	RθJA	50					K/W		
Operating Temperature Range	Tj	-65 to +125					°C		
Storage Temperature Range	Тѕтс	-65 to +150					°C		

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.



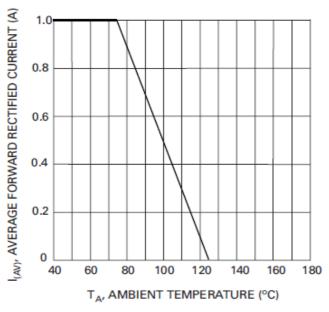


Fig. 1 Forward Current Derating Curve

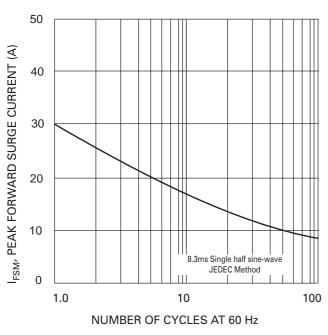


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

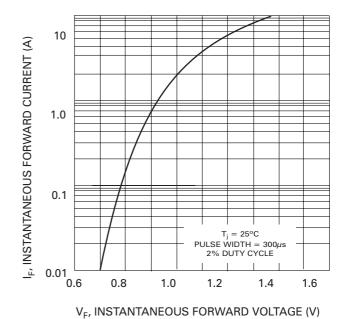


Fig. 2 Typical Forward Characteristics

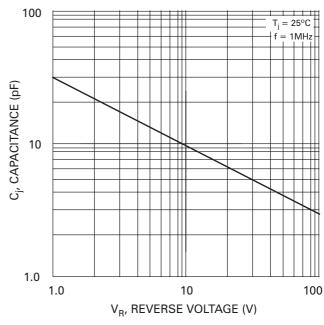


Fig. 4 Typical Junction Capacitance